Unit in mm

TOSHIBA Photocoupler GaAlAs Ired & Photo-IC

# **TLP2200**

Isolated Buss Driver High Speed Line Receiver Microprocessor System Interfaces MOS FET Gate Driver Direct Replacement For HCPL-2200

The TOSHIBA TLP2200 consists of a GaAlAs light emitting diode and integrated high gain, high speed photodetector.

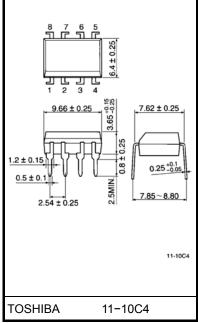
This unit is 8-lead DIP package.

The detector has a three state output stage that eliminates the need for pull-up resistor, and built-in schmitt trigger. The detector IC has an internal shield that provides a guaranteed common mode transient immunity of 1000V/µs.

- Input current:  $I_F = 1.6 \text{mA}$
- Power supply voltage: V<sub>CC</sub> = 4.5~20V
- Switching speed: 2.5MBd guaranteed
- Common mode transient immunity: ±1000V / µs (min.)
- Guaranteed performance over temp: 0~85°C
- Isolation voltage: 2500Vrms(min.)
- UL recognized: UL1577, file No. E67349

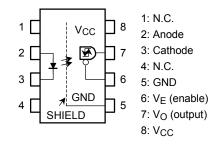
### **Truth Table (positive logic)**

Input	Enable	Output
Н	Н	Z
L	Н	Z
Н	L	Н
L	L	L

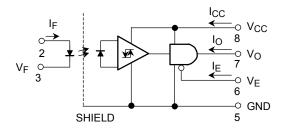


Weight: 0.54 g (typ.)

## Pin Configuration (top view)



### **Schematic**



### **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Input current, on	I <sub>F(ON)</sub>	1.6	1	5	mA
Input current, off	I <sub>F(OFF)</sub>	0	1	0.1	mA
Supply voltage	V <sub>CC</sub>	4.5	1	20	<b>V</b>
Enable voltage high	V <sub>EH</sub>	2.0	1	20	<b>V</b>
Enable voltage low	V <sub>EL</sub>	0	1	0.8	<b>V</b>
Fan out (TTL load)	N	_	_	4	
Operating temperature	T <sub>opr</sub>	0	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

## Absolute Maximum Ratings (no derating required up to 70°C)

	Characteristic	Symbol	Rating	Unit
D	Forward current	ΙF	10	mA
ш	Peak transient forward current (Note 1)	I <sub>FPT</sub>	1	Α
٦	Reverse voltage	$V_{R}$	5	V
ŗ	Output current	Ιο	25	mA
c t o	Supply voltage	V <sub>CC</sub>	-0.5~20	V
Φ	Output voltage	Vo	-0.5~20	V
e t	Three state enable voltage	VE	-0.5~20	V
Ω	Total package power dissipation (Note 2)	PT	210	mW
Оре	rating temperature range	T <sub>opr</sub>	-40~85	°C
Stor	age temperature range	T <sub>stg</sub>	-55~125	°C
Lead	d solder temperature (10s) (**)	T <sub>sol</sub>	260	°C
Isola	ation voltage (AC 1min., R.H. ≤ 60%,Ta = 25°C) (Note 3)	BVS	2500	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- (Note 1) Pulse width 1µs 300pps.
- (Note 2) Derate 4.5mW / °C above 70°C ambient temperature.
- (Note 3) Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5,6,7 and 8 shorted together
  - (\*\*) 1.6mm below seating plane.

# Electrical Characteristics (unless otherwise specified, Ta = $0~85^{\circ}$ C,V<sub>CC</sub> = 4.5~20V, I<sub>F(ON)</sub> = 1.6~5mA, I<sub>F(OFF)</sub> = 0~0.1mA, V<sub>EL</sub> = 0~0.8V,V<sub>EH</sub> = 2.0~20V)

Characteristic	Symbol	Test Condition		Min.	Тур.*	Max.	Unit
Output leakage current (V <sub>O</sub> > V <sub>CC</sub> )	Іонн	I <sub>F</sub> = 5mA, V <sub>CC</sub> = 4.5V	$V_{O} = 5.5V$ $V_{O} = 20V$			100 500	μА
Logic low output voltage	$V_{OL}$	I <sub>OL</sub> = 6.4mA (4 T	TL load)	_	0.32	0.5	٧
Logic high output voltage	V <sub>OH</sub>	I <sub>OH</sub> = -2.6mA		2.4	3.4	ı	<b>V</b>
Logic low enable current	I <sub>EL</sub>	V <sub>E</sub> = 0.4V		_	-0.13	-0.32	mA
Logic high enable current	I <sub>EH</sub>	V <sub>E</sub> = 2.7V V <sub>E</sub> = 5.5V V <sub>E</sub> = 20V			  0.01	20 100 250	μΑ
Logic low enable voltage	V <sub>EL</sub>		_	-	_	0.8	٧
Logic high enable voltage	V <sub>EH</sub>		_	2.0	_	_	V
Logic low supply current	I <sub>CCL</sub>	I <sub>F</sub> = 0mA V <sub>E</sub> = don't care	$V_{CC} = 5.5V$ $V_{CC} = 20V$		5 5.6	6.0 7.5	mA
Logic high supply current	I <sub>CCH</sub>	I <sub>F</sub> = 5mA V <sub>E</sub> = don't care	$V_{CC} = 5.5V$ $V_{CC} = 20V$		2.5 2.8	4.5 6.0	mA
	I <sub>OZL</sub>	I <sub>F</sub> = 5mA V <sub>E</sub> = 2V	V <sub>O</sub> = 0.4V	_	1	-20	
High impedance state output current	I <sub>OZH</sub>	I <sub>F</sub> = 0mA V <sub>E</sub> = 2V	$V_O = 2.4V$ $V_O = 5.5V$ $V_O = 20V$		_ _ 0.01	20 100 500	μΑ
Logic low short circuit output current (Note 4)	I <sub>OSL</sub>	I <sub>F</sub> = 0mA	$V_O = V_{CC} = 5.5V$ $V_O = V_{CC} = 20V$	25 40	55 80		mA
Logic high short circuit output current (Note 4)	I <sub>OSH</sub>	I <sub>F</sub> = 5mA V <sub>O</sub> = GND	$V_{CC} = 5.5V$ $V_{CC} = 20V$	-10 -25	-25 -60	_	mA
Input current hysteresis	I <sub>HYS</sub>	V <sub>CC</sub> = 5V	1 00	_	0.05	_	mA
Input forward voltage	V <sub>F</sub>	I <sub>F</sub> = 5mA, Ta = 25°C		_	1.55	1.7	V
Temperature coefficient of forward voltage	ΔV <sub>F</sub> / ΔTa	I <sub>F</sub> = 5mA		_	-2.0	_	mV / °C
Input reverse breakdown voltage	BV <sub>R</sub>	I <sub>R</sub> = 10μA, Ta = 25°C		5	_	_	٧
Input capacitance	C <sub>IN</sub>	V <sub>F</sub> = 0V, f = 1MHz, Ta = 25°C		_	45	_	pF
Resistance (input-output)	$R_{I-O}$	V <sub>I-O</sub> = 500V R.H. ≤ 60% (Note 3)		5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
Capacitance (input-output)	$C_{I-O}$	$V_{I-O} = 0V, f = 1MHz$ (Note 3)		_	0.6	_	pF

<sup>(\*\*)</sup> All typ. values are at Ta = 25°C,  $V_{CC}$  = 5V,  $I_{F(ON)}$  = 3mA unless otherwise specified.

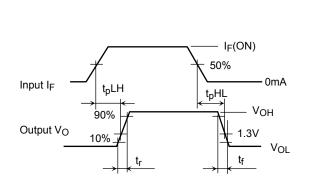
# Switching Characteristics (unless otherwise specified, Ta = 0~85°C, $V_{CC} = 4.5~20$ V, $I_{F(ON)} = 1.6~5$ mA, $I_{F(OFF)} = 0~0.1$ mA)

Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time to logic high output level		t <sub>pLH</sub>		Without peaking capacitor C <sub>1</sub>	_	235	_	ns
	(Note 5)	·		With peaking capacitor C <sub>1</sub>	_	_	400	
Propagation delay time to logic low output level		$t_{pHL}$	1	Without peaking capacitor C <sub>1</sub>	_	250	_	ns
	(Note 5)	·		With peaking capacitor C <sub>1</sub>		-	400	
Output rise time (10-90%)		t <sub>r</sub>			_	35	_	ns
Output fall time (90–10%)		t <sub>f</sub>		_	_	20	_	ns
Output enable time to logic high		t <sub>pZH</sub>		_	_	_	_	ns
Output enable time to logic low		$t_{pZL}$	2	_		-	_	ns
Output disable time from logic high		t <sub>pHZ</sub>	2	_	_	1	_	ns
Output disable time from logic low		$t_{pLZ}$		_		1	_	ns
Common mode transient immunity at logic high output	(Note 6)	CM <sub>H</sub>	3	I <sub>F</sub> = 1.6mA, V <sub>CM</sub> = 50V, Ta = 25°C	-1000	-	_	V / µs
Common mode transient immunity at logic low output	(Note 6)	CML	3	$I_F = 0$ mA, $V_{CM} = 50$ V, $Ta = 25$ °C	1000		_	V / µs

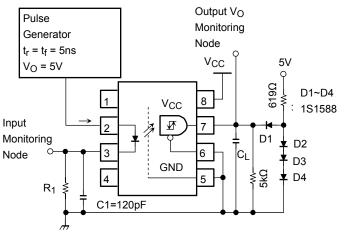
<sup>(\*)</sup> All typ. values are at Ta = 25°C,  $V_{CC}$  = 5V,  $I_{F(ON)}$  = 3mA unless otherwise specified.

- (Note 4) Duration of output short circuit time should not exceed 10ms.
- (Note 5) The  $t_{pLH}$  propagation delay is measured from the 50% point on the leading edge of the input pulse to the 1.3V point on the leading edge of the output pulse.
  - The  $t_{\text{pHL}}$  propagation delay is measured from the 50% point on the trailing edge of the input pulse to the 1.3V point on the trailing edge of the output pulse.
- (Note 6) CM<sub>L</sub> is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic low state ( $V_O \le 0.8V$ ).
  - $CM_H$  is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic high state ( $V_O \le 2.0V$ ).

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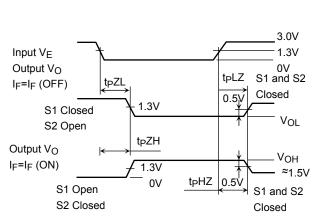


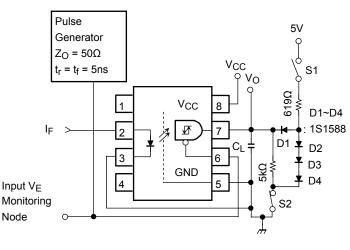
R <sub>1</sub>	2.15kΩ	1.1kΩ	681Ω
I <sub>F</sub> (ON)	1.6mA	3mA	5mA



 ${\sf C}_1$  is peaking capacitor. The probe and jig capacitances are include in  ${\sf C}_1$ .  ${\sf C}_L$  is approximately 15pF which includes probe and stray wiring capacitance.

# Test Circuit 2 $\ t_{pHZ,}\,t_{pZH,}\,t_{pLZ}$ and $t_{pZL}$

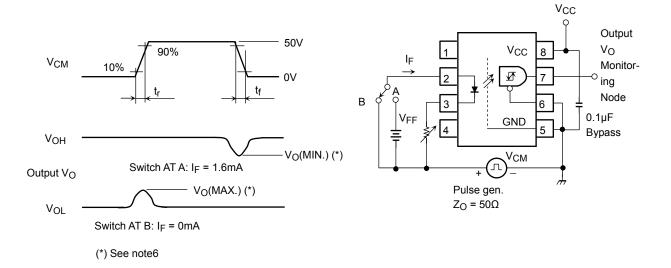




C<sub>L</sub> is approximately 15pF which includes probe and stray wiring capacitance.

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# **Test Circuit 3 Common Mode Transient Immunity**



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